

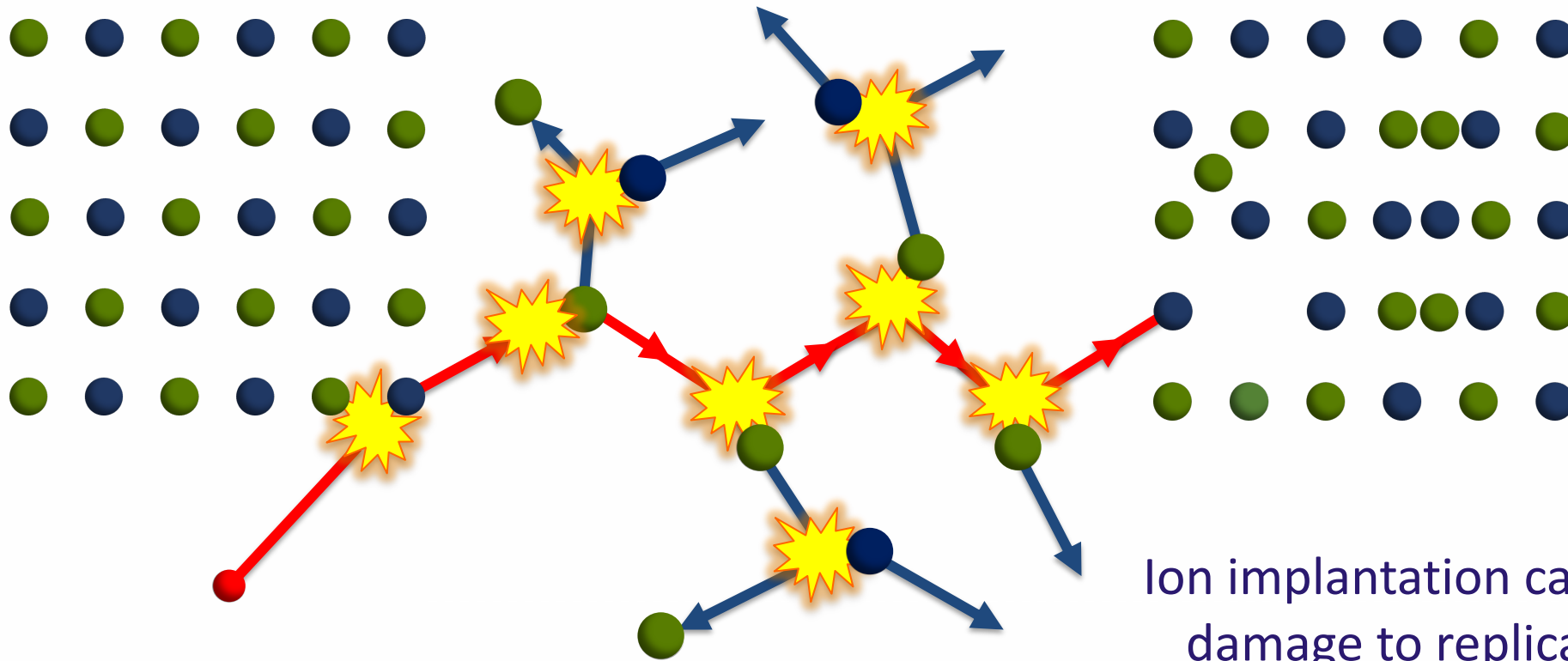
Grazing incidence XRD to investigate ion implantation induced damage

Amy Gandy

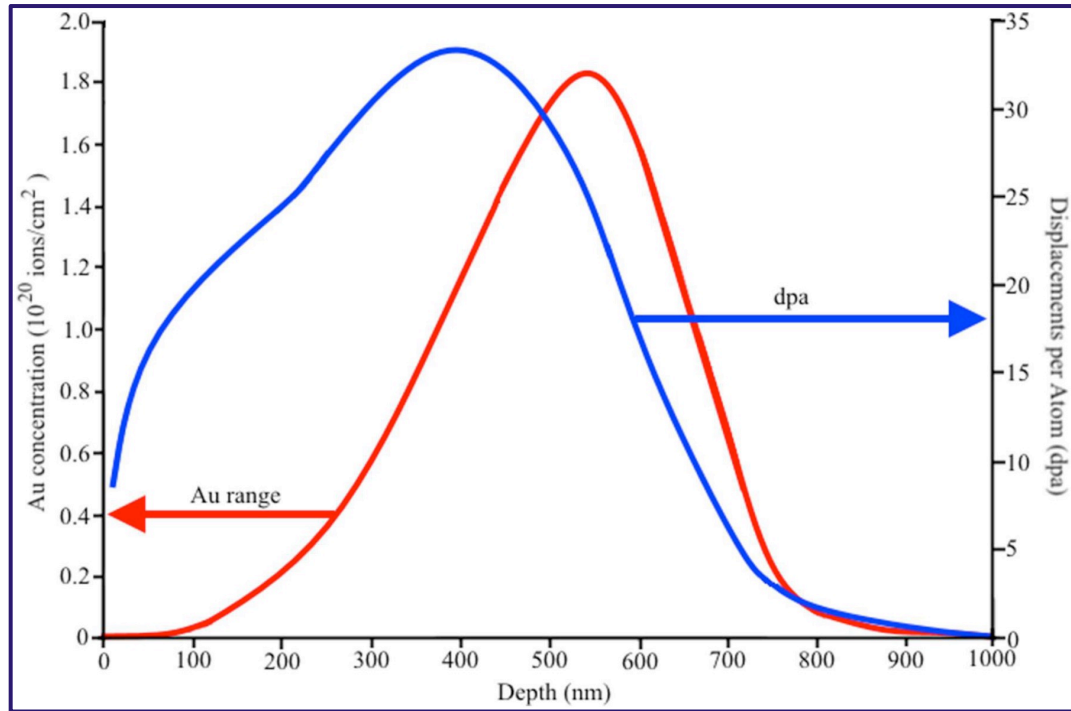
Royce Technology Platform Lead in Advanced Characterisation of Radiation
Damage in Materials

Department of Materials Science and Engineering, University of Sheffield

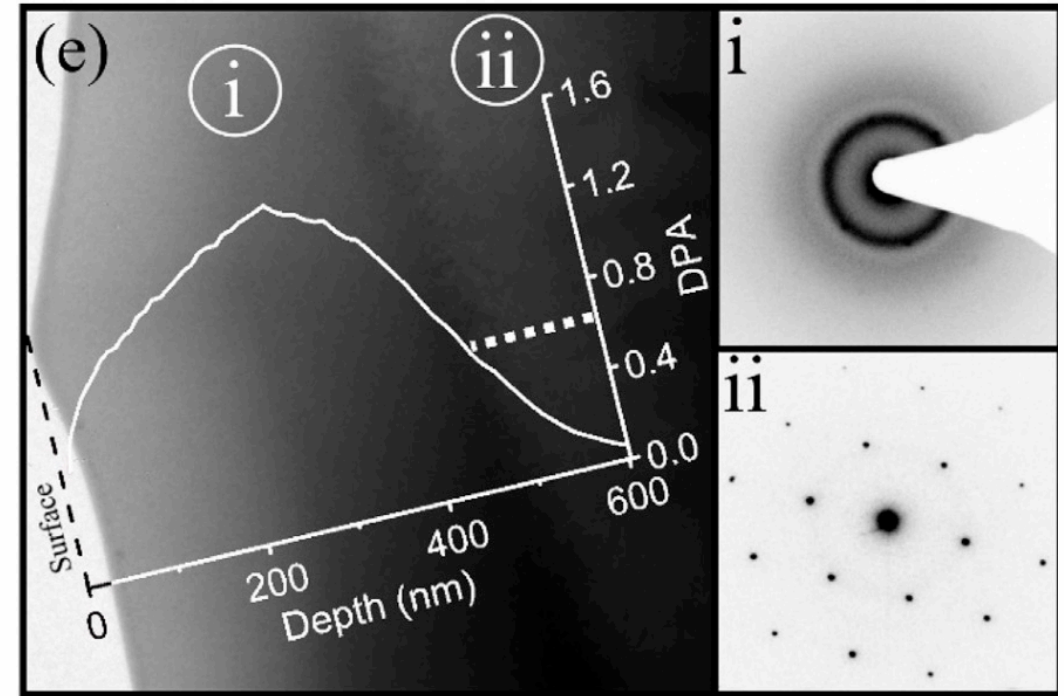
Implantation induced damage



Ion implantation can induce displacement damage to replicate (ish!) the damage produced by nuclear reactions.

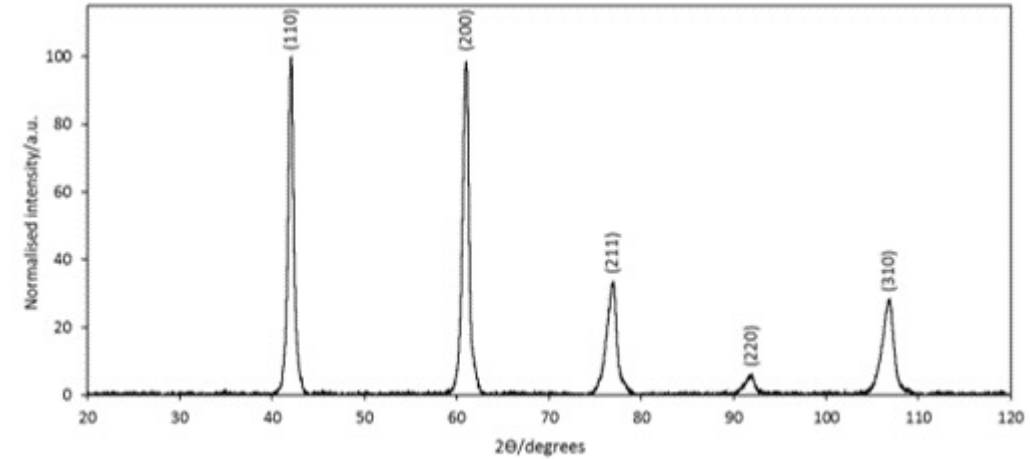
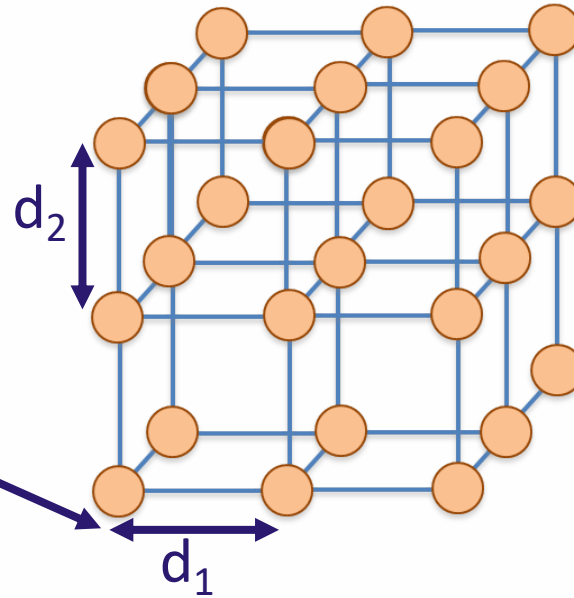
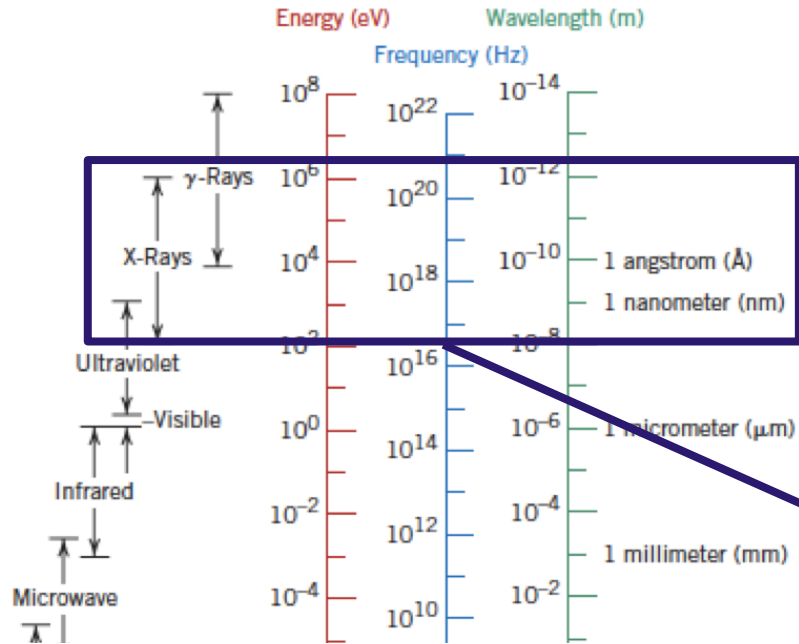


SRIM simulation of 5 MeV Au²⁺ ion implantation to a fluence of 5×10^{15} Au ions/cm² into a SiFeVCrMo alloy.



Cross-sectional TEM (XTEM) gives excellent information on implantation induced structural transformations, but requires extensive training!

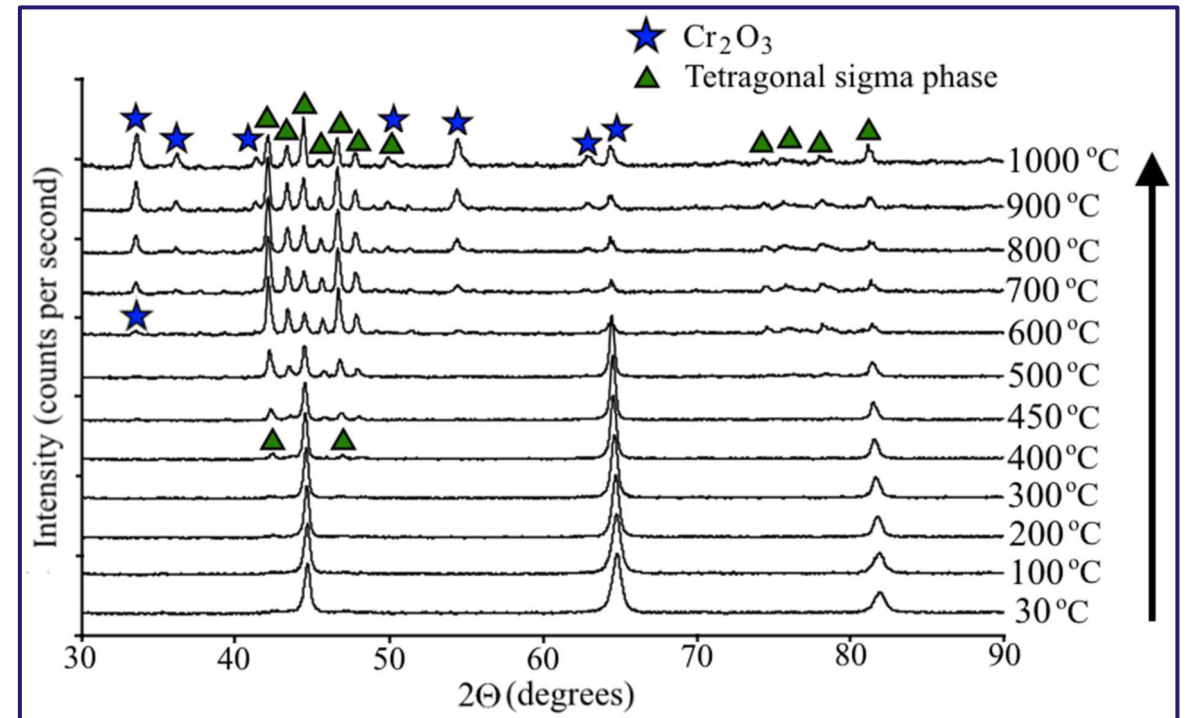
Ion Beam Irradiation and Characterisation: Best Practice
Manchester, March 2nd – 3rd 2023



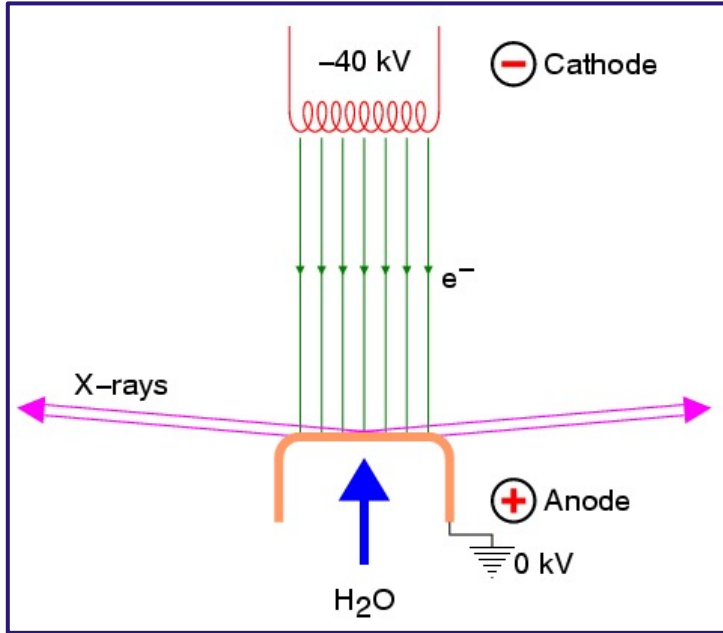
X-ray wavelength range $0.01 < \lambda < 100 \text{ \AA} \approx$ interatomic distances in a crystal.

XRD can be used to:

- Identify phases by comparison with data from known structures,
- Quantify changes in the cell parameters (e.g., cell volume, interatomic spacing),
- Determine crystallite size
- Determine crystallographic structure (cell parameters, space group, atomic coordinates) of novel or unknown crystalline materials.
- Determine temperature induced phase transformations.



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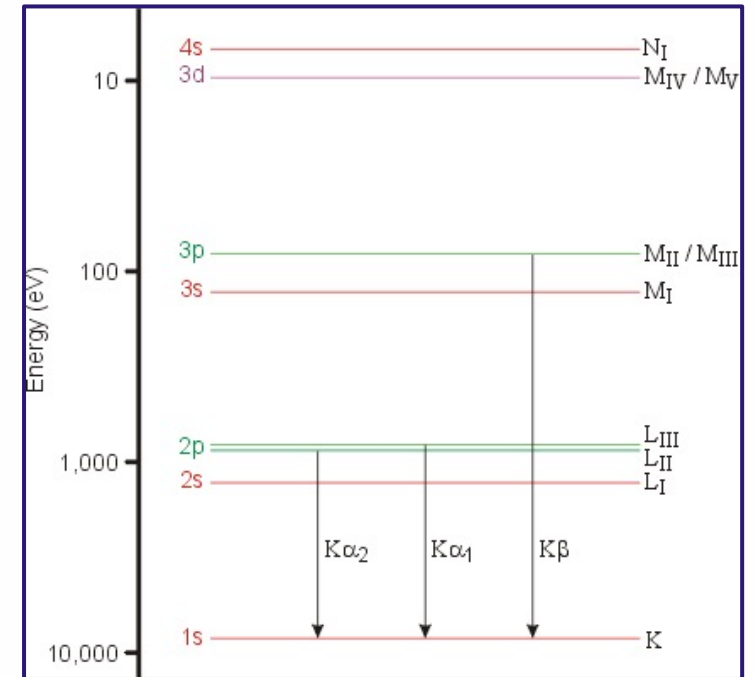
<http://pd.chem.ucl.ac.uk/pdnn/inst1/xtube.htm>

X-rays are generated by heating a filament (e.g., W) to emit electrons which are directed onto a target (e.g., Cu).

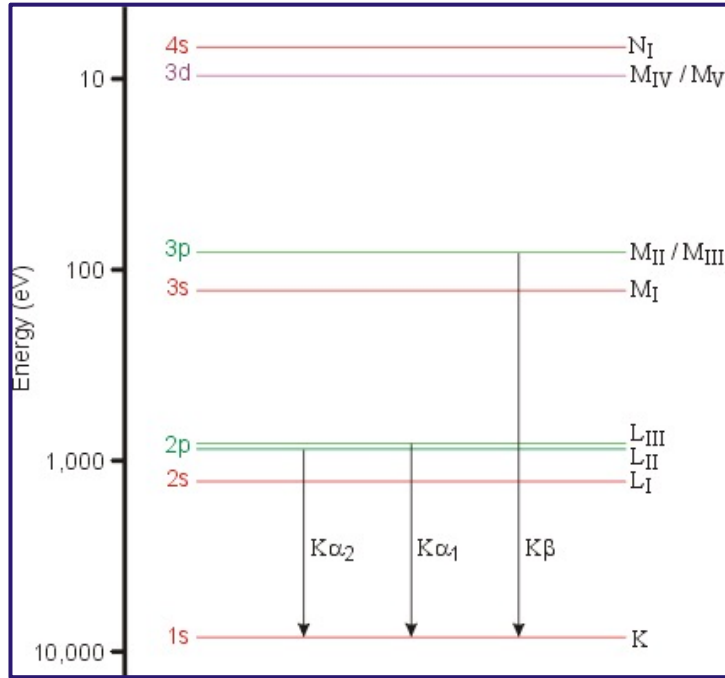
Interaction with core shell electrons in the target results in ionisation.

An electron from a higher energy level drops to the lower energy level, emitting a *characteristic X-ray*, with specific energy and wavelength.

$$\Delta E = E_L - E_K$$



<http://pd.chem.ucl.ac.uk/pdnn/inst1/xrays.htm>



<http://pd.chem.ucl.ac.uk/pdnn/inst1/xrays.htm>

K_{α} L \rightarrow K transitions

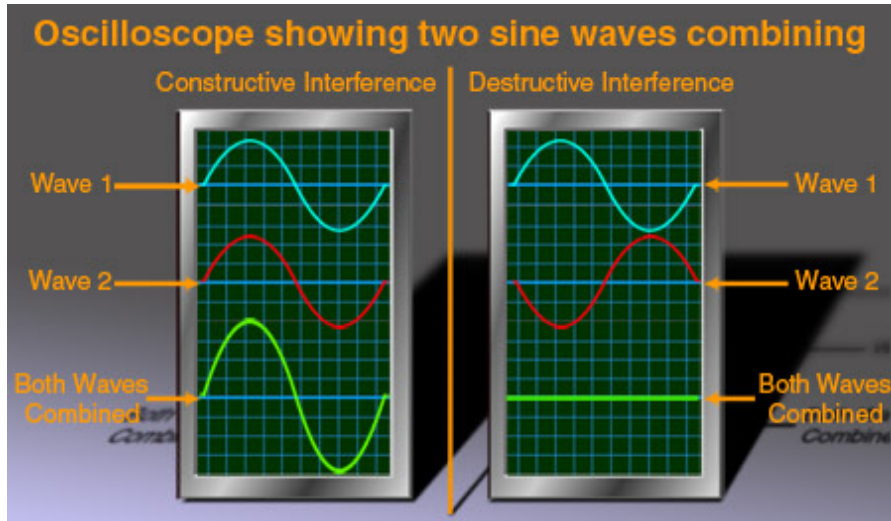
K_{β} M \rightarrow K transitions

Cu source:

$K_{\alpha} = 1.54184 \text{ \AA}$

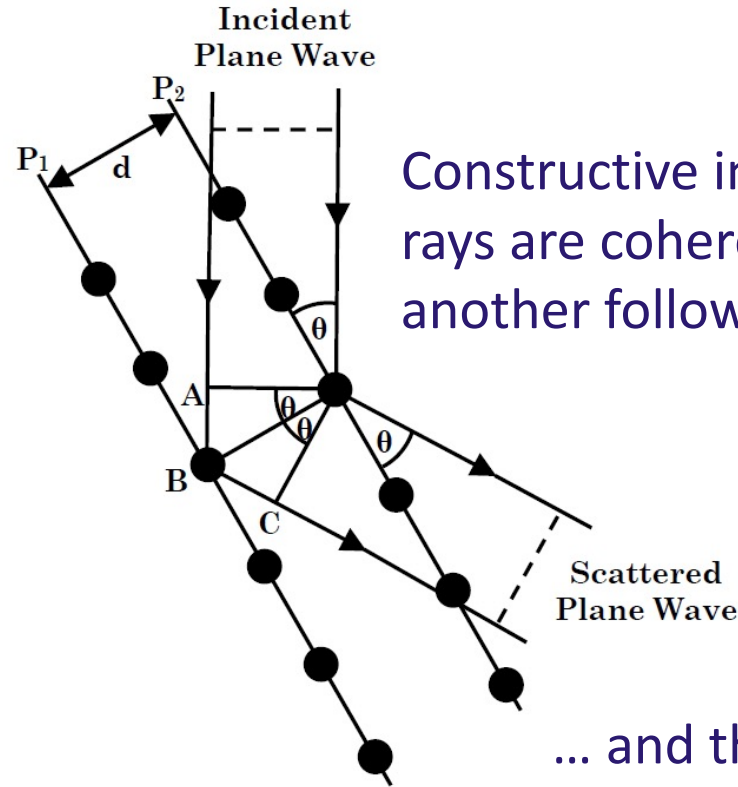
$K_{\beta} = 1.39222 \text{ \AA}$

Want monochromatic X-rays, so use a filter to suppress Cu K_{β} transitions...



<http://salfordacoustics.co.uk/sound-waves/superposition>

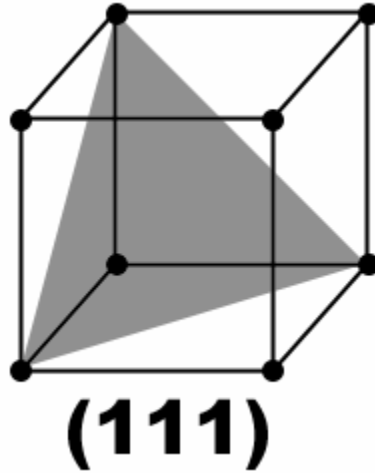
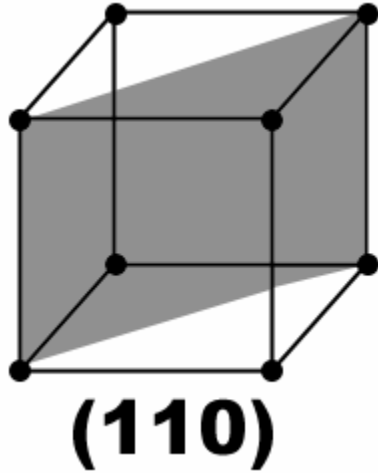
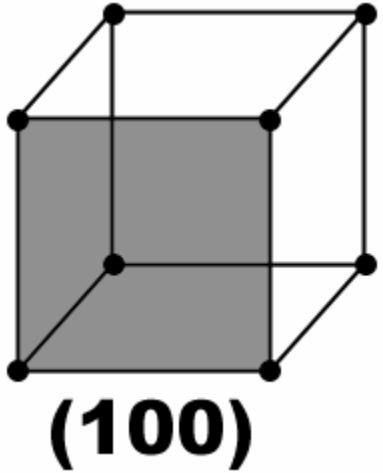
Diffraction patterns are only produced when the diffracted X-rays interfere constructively.



Constructive interference only occurs if the X-rays are coherent and remain in phase with one another following diffraction...

... and these conditions are only realised when the X-rays are diffracted through specific angles:

$$n \lambda = 2 d \sin \theta$$

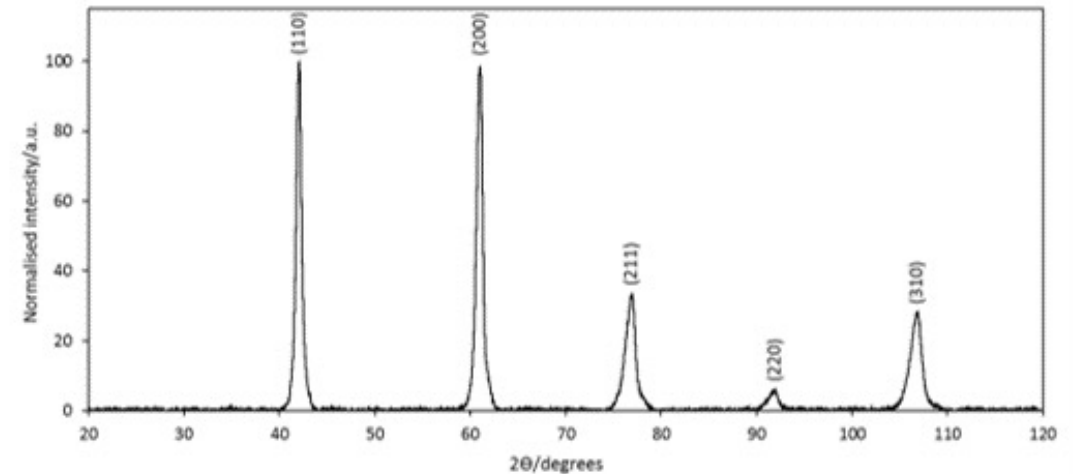


$$n \lambda = 2 d \sin \theta$$

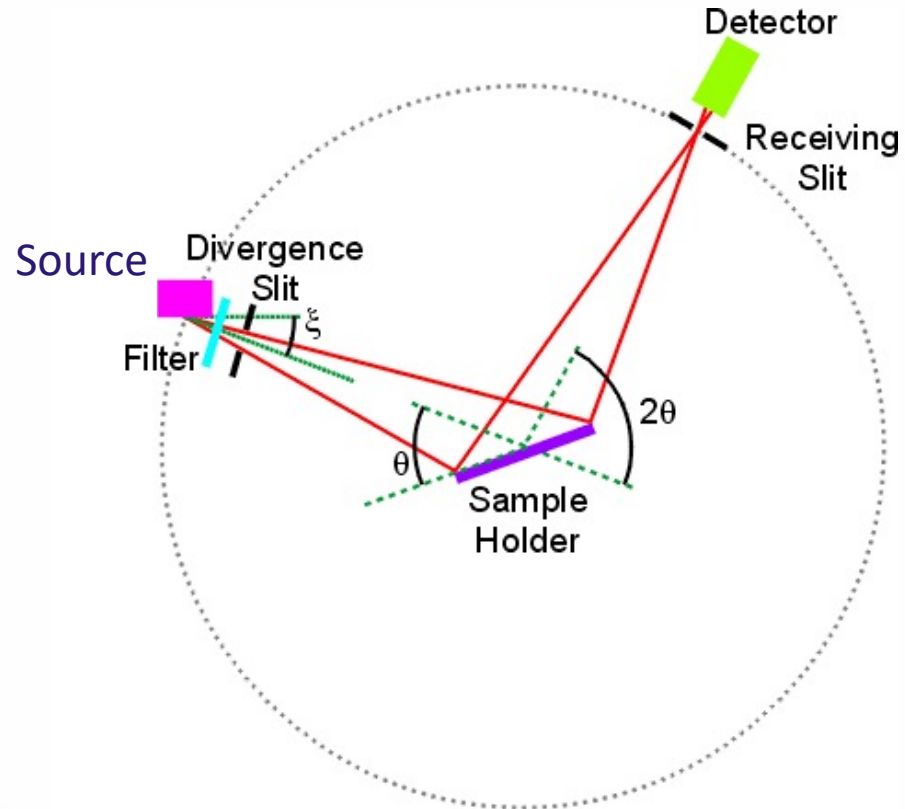
Recording the angles at which diffracted waves are observed gives a diffraction pattern which is unique to the material:

We use Bragg's Law to predict the angles through which X-rays will be diffracted from a set of lattice planes.

The diffracted angles are determined by the distances between parallel planes of atoms.



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<http://pd.chem.ucl.ac.uk/pdnn/inst1/optics1.htm>

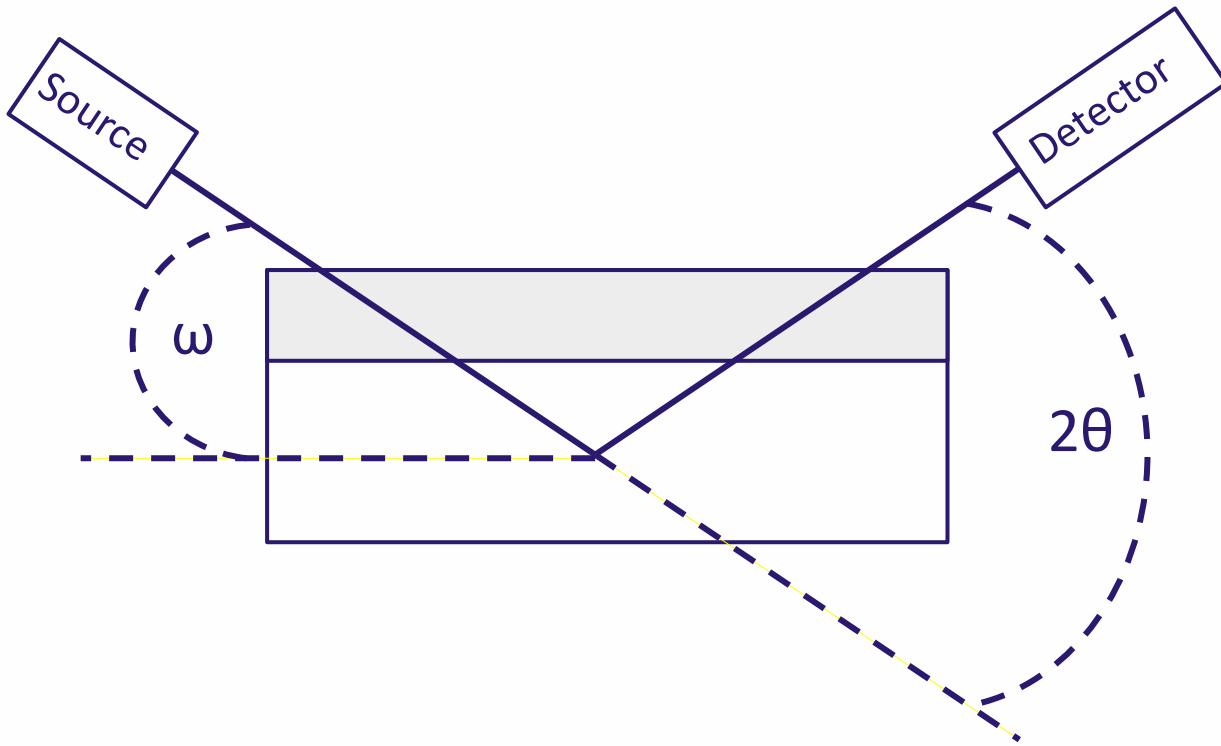
X-rays are divergent when produced.

Bragg-Brentano geometry “focuses” the divergent and diffracted beams using Soller slits.

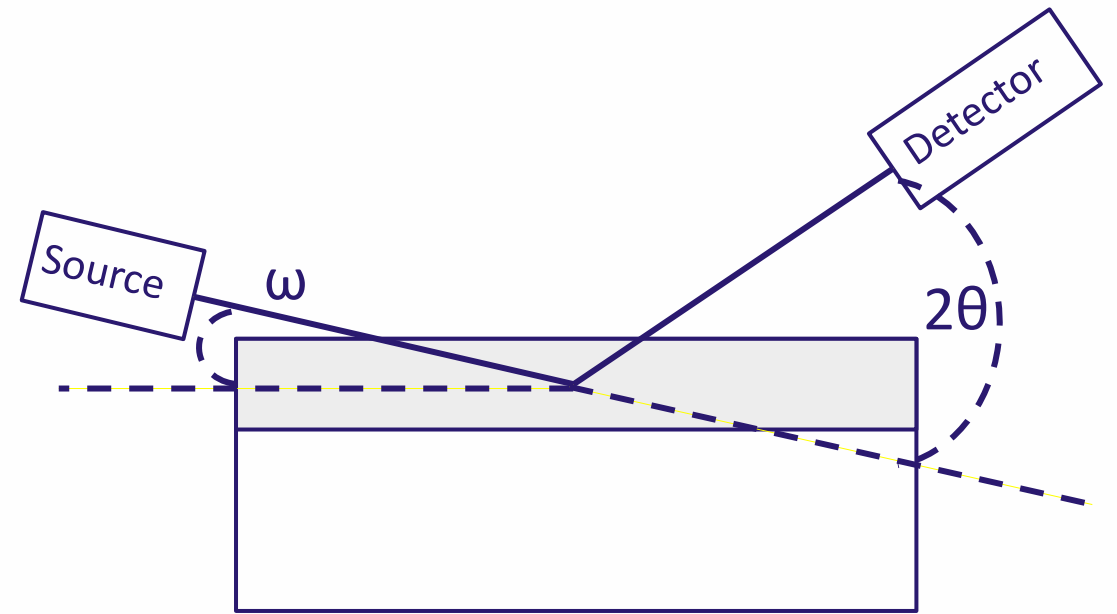
Divergence slit determines the X-ray “footprint” on the sample.

Both the source and the detector move by $-\theta$ and θ in this geometry.

The X-ray may probe too deeply to study ion implantation induced damage.



X-ray source and detector move



X-ray source does not move $\rightarrow \omega$ is small and constant.

Detector moves through 2θ .

The angle, ω , required for the X-rays to penetrate into a specific region beneath the surface is calculated by:

$$\omega = \sin^{-1} \left(\frac{x}{3\mu} \right)$$

Where x is the thickness of the region (i.e., the implanted region), and μ is the attenuation length of the material, which is **dependant on the density and composition of the material and X-ray energy**.

μ measures the exponential decay of X-ray intensity as it passes through a material.

μ is defined as the length travelled before the X-ray intensity falls to $1/e$ of its original value.

Aim to probe a depth of 3μ , where there has been $> 95 \%$ attenuation of incident X-rays in the defined thickness.

Calculation of a compounds attenuation length is determined through addition of μ values of each individual element, multiplied by a weight fraction term.

μ for your material can be calculated using for example the Hephaestus software package, or:
https://henke.lbl.gov/optical_constants/atten2.html

Si 2.3at% - Fe 36.9 at% - V 14.79 at% - Cr 35.09 at% - Mo 10.92 at%;

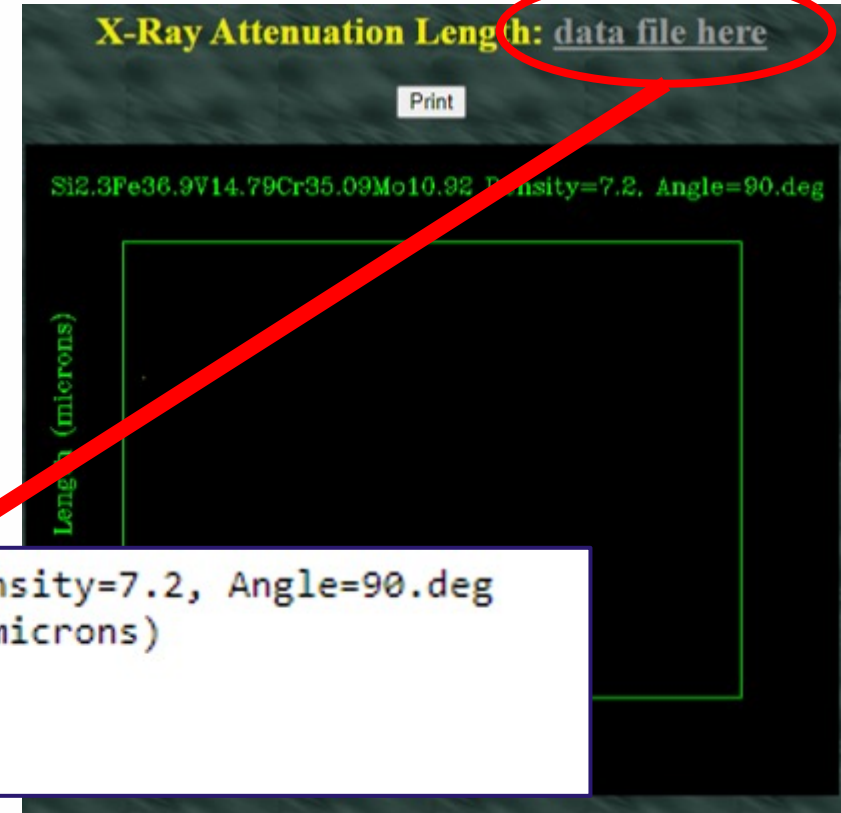
Density = 7.2 gcm⁻³

Cu K_α = 1.544 Å = 8.03 KeV = 8030 eV

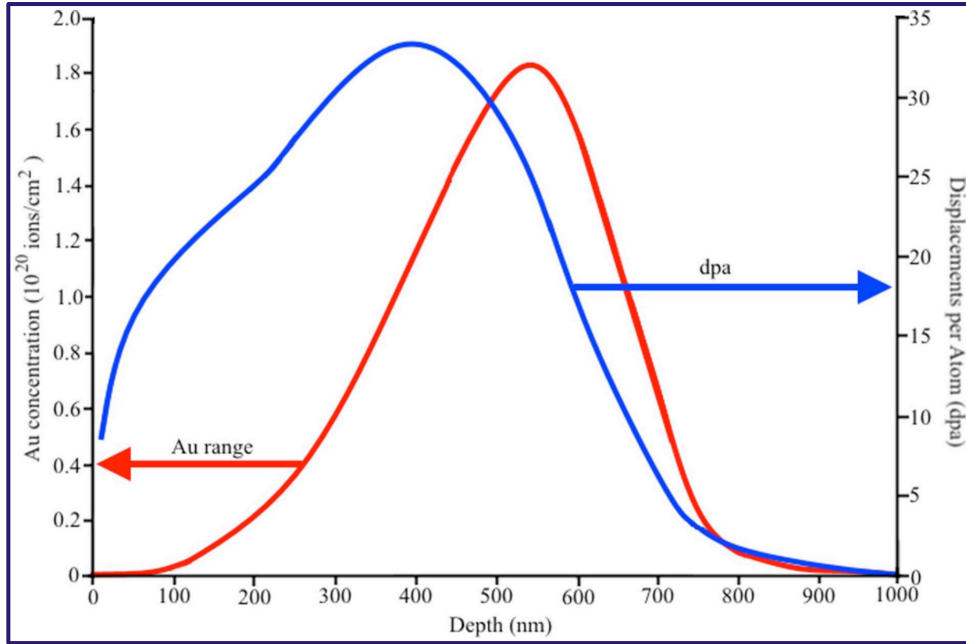
- Choose from a list of common materials:
- Chemical Formula:
- Density: gm/cm³ (enter negative value to use tabulated values.)
- Scan from to in steps (< 500).
(NOTE: Energies must be in the range 30 eV < E < 30,000 eV, Wavelength between 0.041
- At fixed =

To request a press this button:

To reset to default values, press this button:



Photon Energy (eV)	Atten Length (microns)
8030.00	5.68297
8030.00	5.68297
8030.00	5.68297



SRIM simulation of 5 MeV Au²⁺ ion implantation to a fluence of 5 x 10¹⁵ Au ions/cm² into a SiFeVCrMo alloy.

$$\omega = \sin^{-1} \left(\frac{x}{3\mu} \right)$$

$$\omega = \sin^{-1} \left(\frac{500}{3 \times 5683} \right)$$

Grazing Incident Angles for XRD			
SiFeVCrMo	Density = 7.2 g.cm-3		Probe Depth
Energy Cu k alpha	8030 eV	Thickness of damaged region (nm)	500
Absorption length in SiFeVCrMo (nm)	5683	GI angle	1.681

Instrument details:

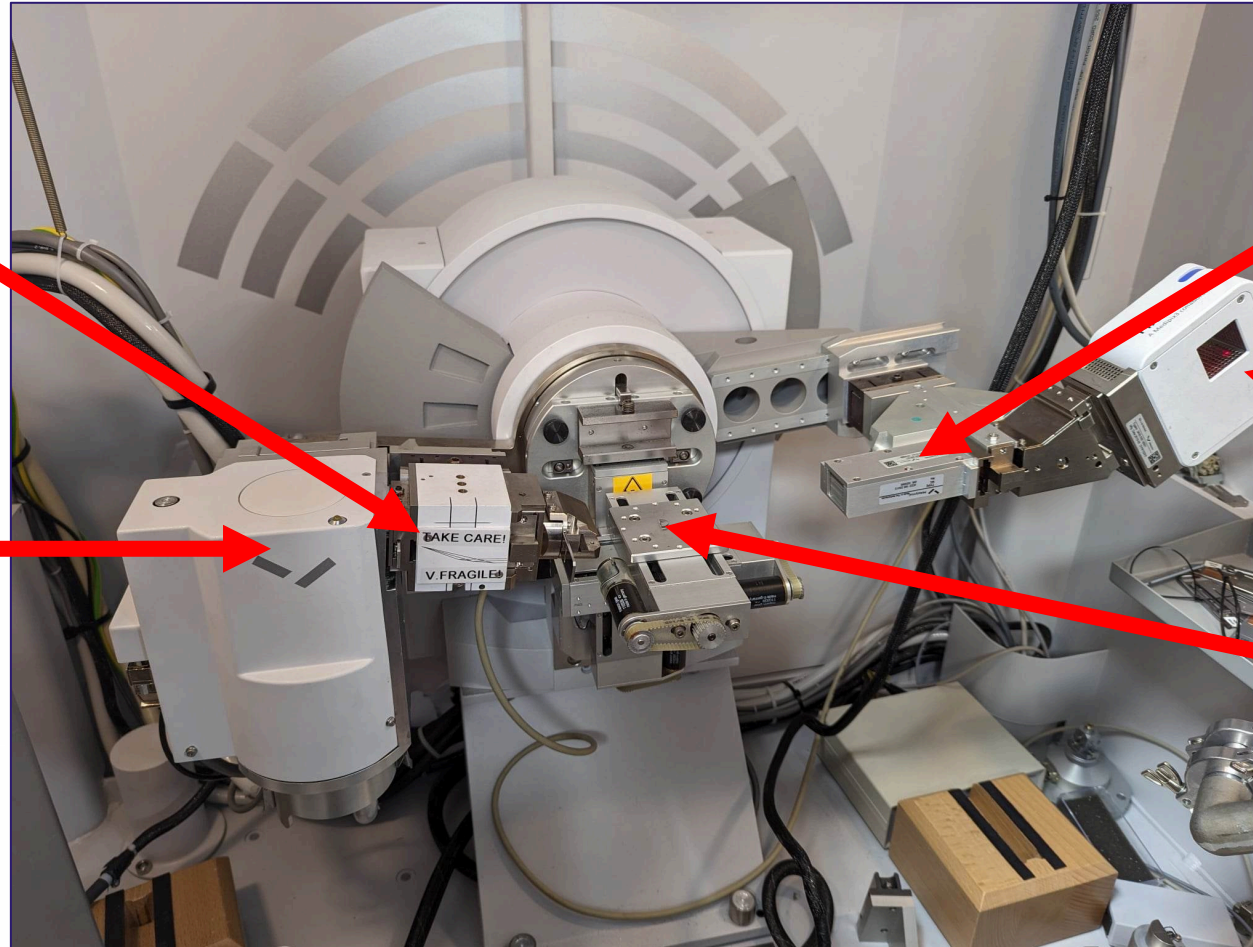
- Cu X-ray source (1.544 Å).
- Ni Kbeta filter.
- Programmable divergence and acceptance slit.
- Goebel mirror.
- PIXcel1D detector.
- 0.27 parallel plate collimator with secondary beam monochromator.
- 45 position sample changer.

Applications:

- Grazing incidence XRD (GIXRD).
- X-ray reflectometry (XRR).
- Texture and stress analysis.
- High temperature XRD.



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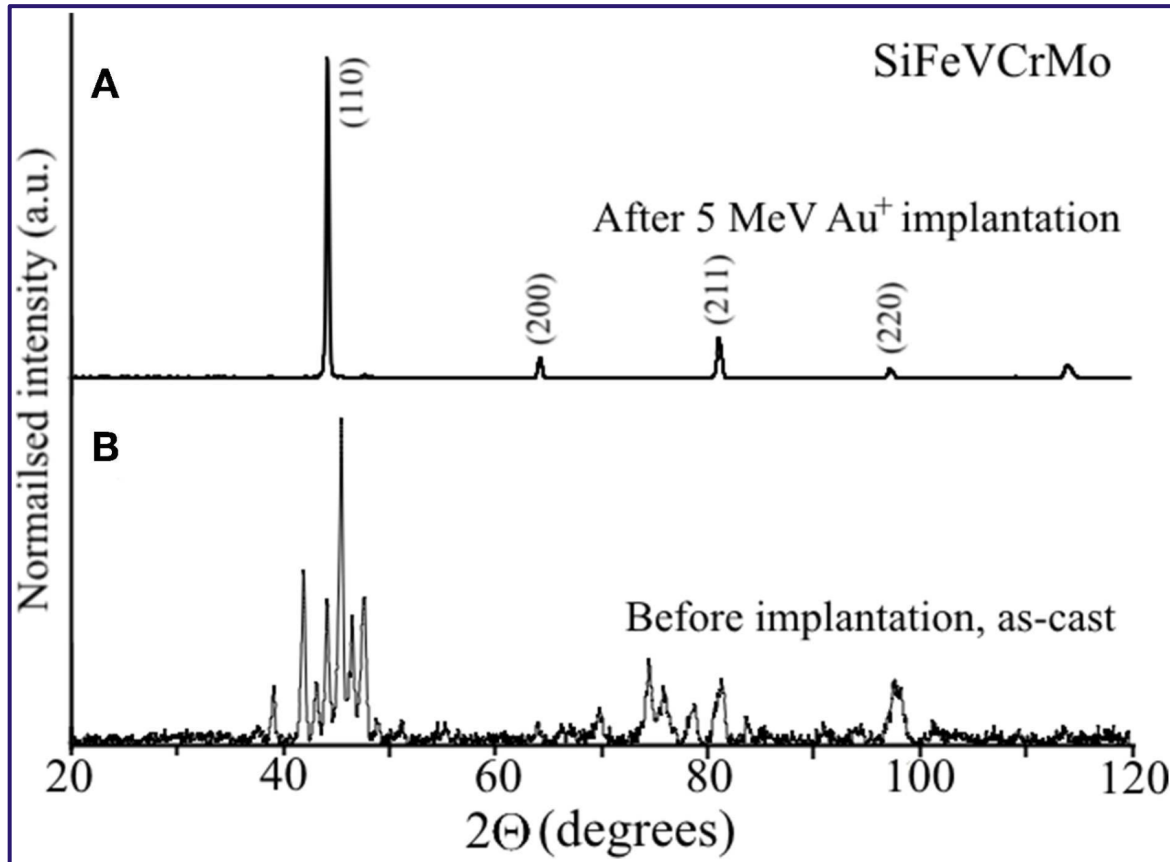
Parallel beam mirror

Parallel plate collimator

Detector moves through 2θ

Fixed ω at e.g., 1.681°

Sample



Room temperature grazing incidence XRD patterns from SiFeVCrMo, (B) before and (A) after room temperature ion implantation with 5 MeV Au²⁺ ions, to a fluence of 5×10^{15} Au²⁺ ions/cm².

GIXRD patterns show a transformation from tetragonal to BCC structure following ion implantation.

Phase analysis used the International Center for Diffraction Data's (ICDD) PDF-4+ database.

A S. Gandy, B Jim, G Coe, D Patel, L Hardwick, Sh Akhmadaliev, N Reeves-McLaren, R Goodall; High temperature and ion implantation induced phase transformations in novel reduced activation Si-Fe-V-Cr (-Mo) high entropy alloys, *Frontiers in Materials* (2019)

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$\text{Ca}_{1-x}\text{La}_{2x/3}\text{TiO}_3$ ceramic system used to determine the link between cation vacancies in perovskites and radiation damage resistance (from 1 MeV Kr^+ ions).

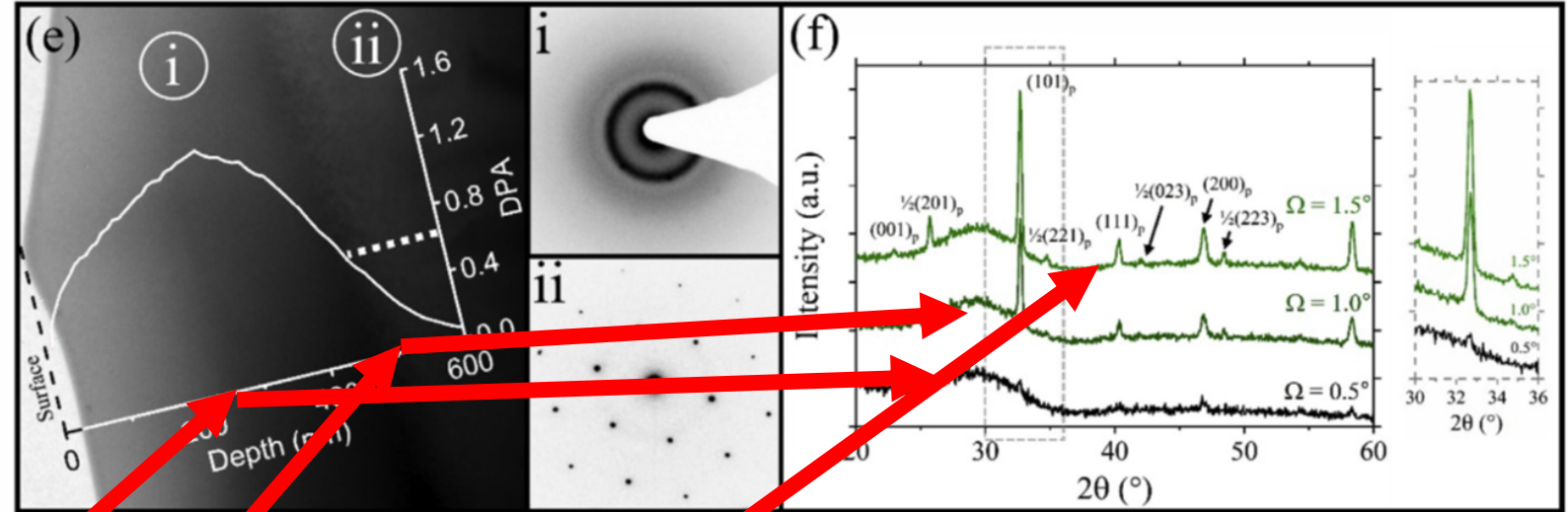
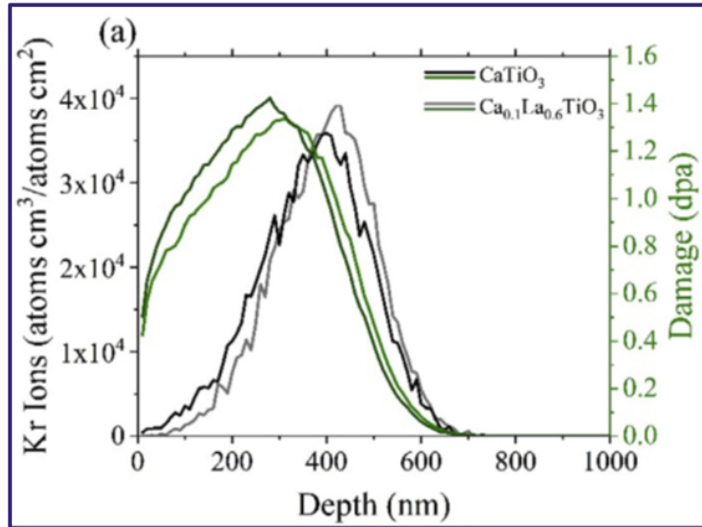
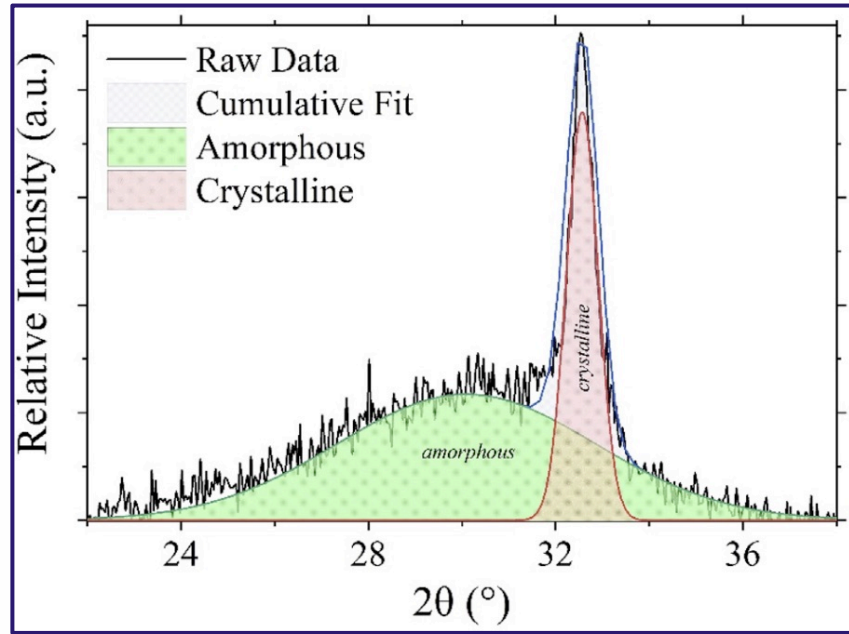


Table 1
X-ray penetration depths for $\text{Ca}_{1-x}\text{La}_{2x/3}\text{TiO}_3$ samples as calculated using equation (1) for the three incident angles. Errors represent small variations in density across pellets.

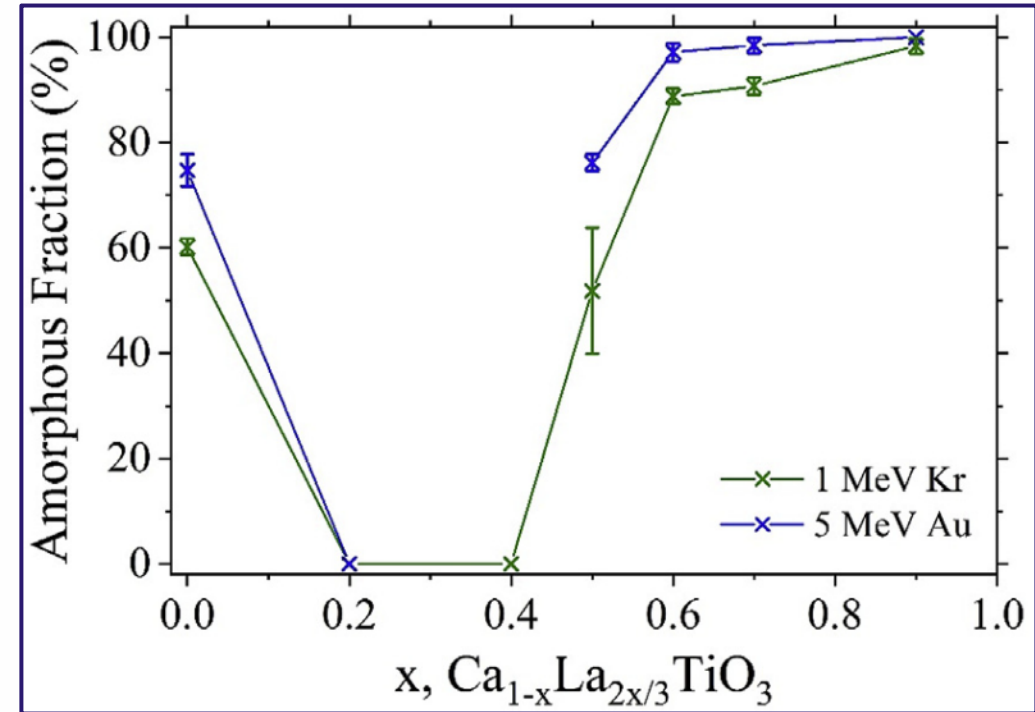
x	X-ray Penetration Depth, τ (± 10 nm)		
	$\Omega = 0.5^\circ$	1.0°	1.5°
0	450	900	1350
0.2	420	840	1260
0.4	360	720	1080
0.5	310	620	930
0.6	300	600	900
0.7	280	560	840
0.9	250	500	750

S M Lawson, N C Hyatt, K R Whittle, A S Gandy; Resistance to amorphisation in $\text{Ca}_{1-x}\text{La}_{2x/3}\text{TiO}_3$ perovskites – a bulk ion-irradiation study, Acta Materialia (2019)

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A pseudo-Voigt peak fit to determine crystalline and amorphous fractions produced in ion implanted materials.



S M Lawson, N C Hyatt, K R Whittle, A S Gandy; Resistance to amorphisation in $\text{Ca}_{1-x}\text{La}_{2x/3}\text{TiO}_3$ perovskites – a bulk ion-irradiation study, Acta Materialia (2019)



Applications:

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- X-ray reflectometry (XRR).
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- High temperature XRD.

Other machines are available through Royce:

<https://www.sheffield.ac.uk/royce-institute/x-ray>